

Device Modeling Report

COMPONENTS:

DIODE/GENERAL PURPOSE RECTIFIER/PROFESSIONAL

PART NUMBER: YG963S6R

MANUFACTURER: Fuji Electric

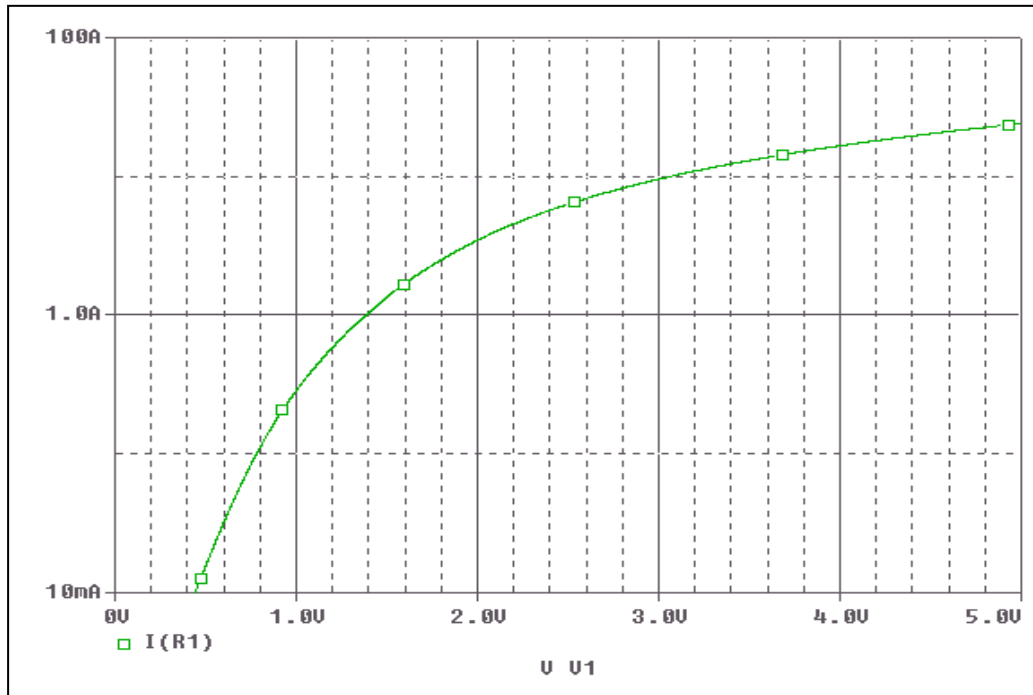


Bee Technologies Inc.

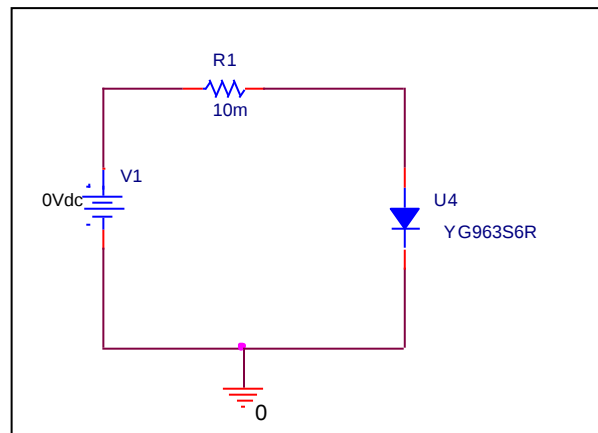
Pspice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

Forward Current Characteristic

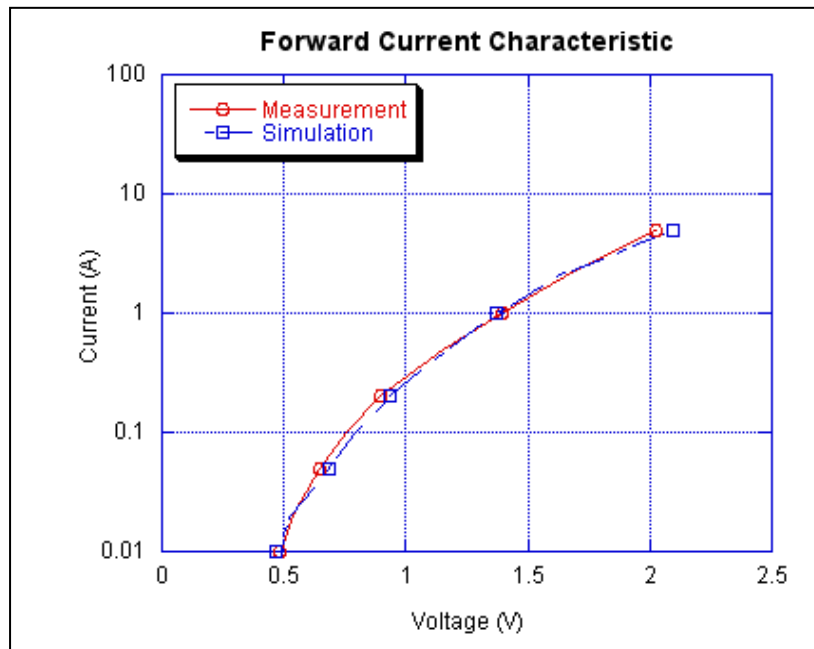
Circuit Simulation Result



Evaluation circuit



Comparison graph

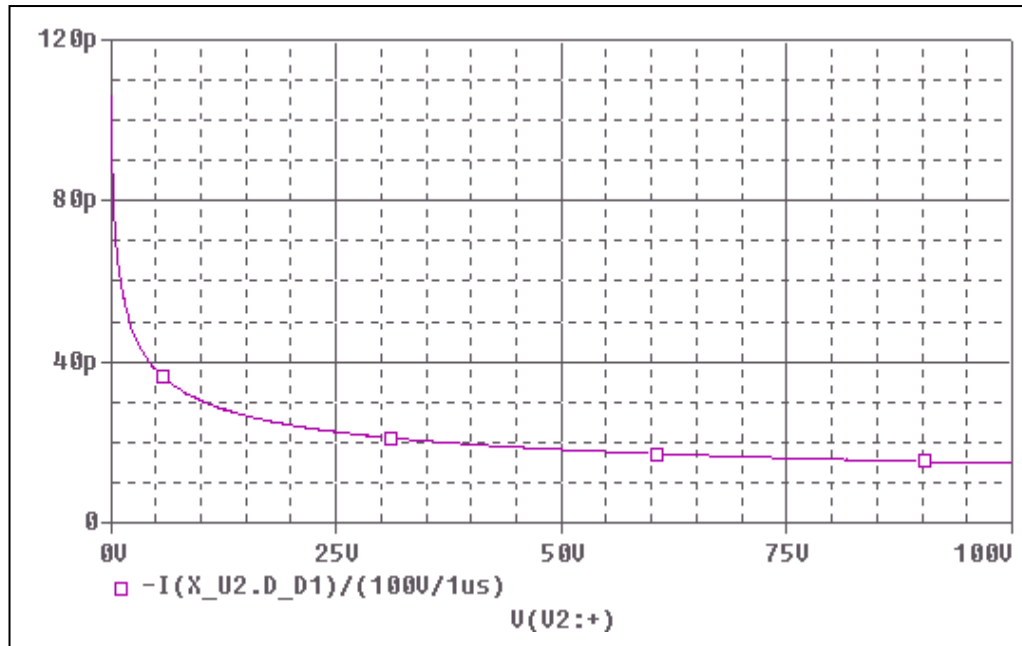


Simulation Result

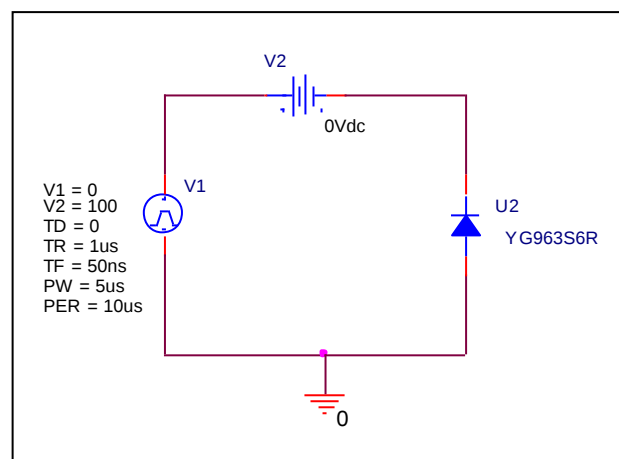
Ifwd (A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.01	0.485	0.465	4.124
0.02	0.535	0.533	0.374
0.05	0.645	0.664	-2.946
0.1	0.755	0.778	-3.046
0.2	0.895	0.936	-4.581
0.5	1.155	1.165	-0.883
1	1.395	1.369	1.900
2	1.650	1.621	1.776
5	2.025	2.0946	-3.437

Junction Capacitance Characteristic

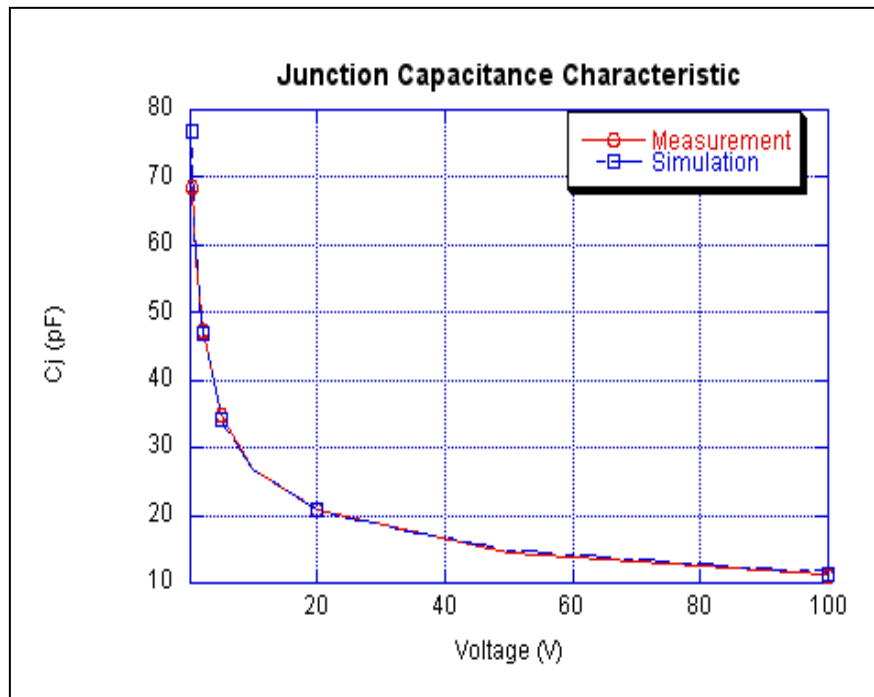
Circuit simulation result



Evaluation circuit



Comparison graph

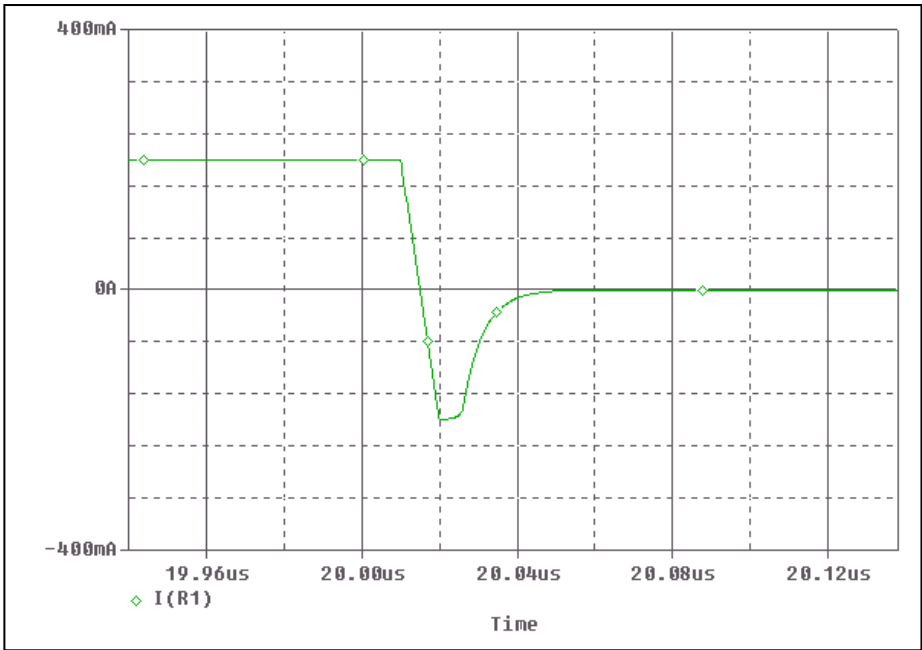


Simulation Result

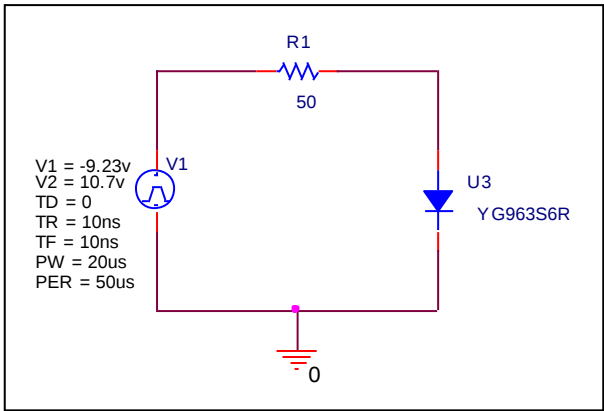
Vrev (V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0.5	68.434	76.704	-12.084
1	58.067	59.599	-2.638
2	47.267	46.928	0.718
5	34.802	34.346	1.309
10	26.985	26.970	0.057
20	20.749	20.753	-0.018
50	14.559	14.680	-0.834
100	11.096	11.275	-1.611

Reverse Recovery Characteristic

Circuit simulation result



Evaluation circuit

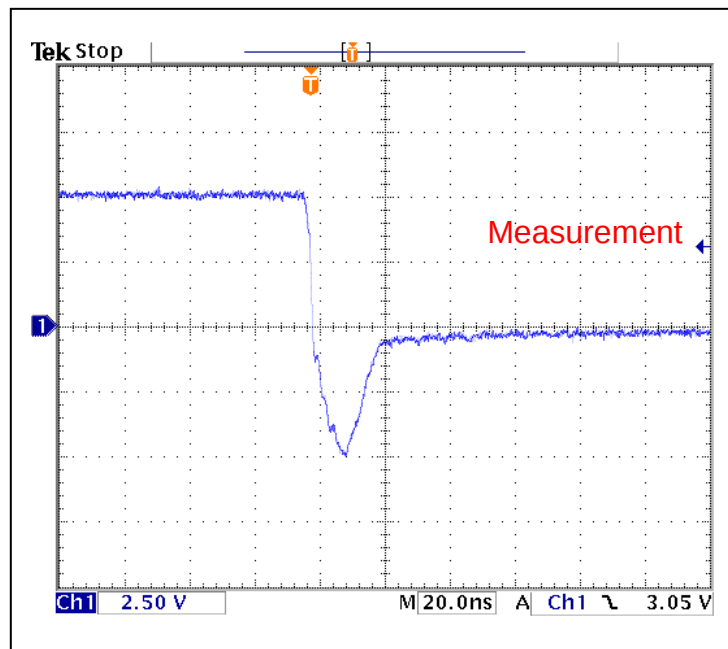


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
Trj	9.600	ns	9.694	ns	-0.979
Trb	12.400	ns	12.607	ns	-1.669

Reverse Recovery Characteristic

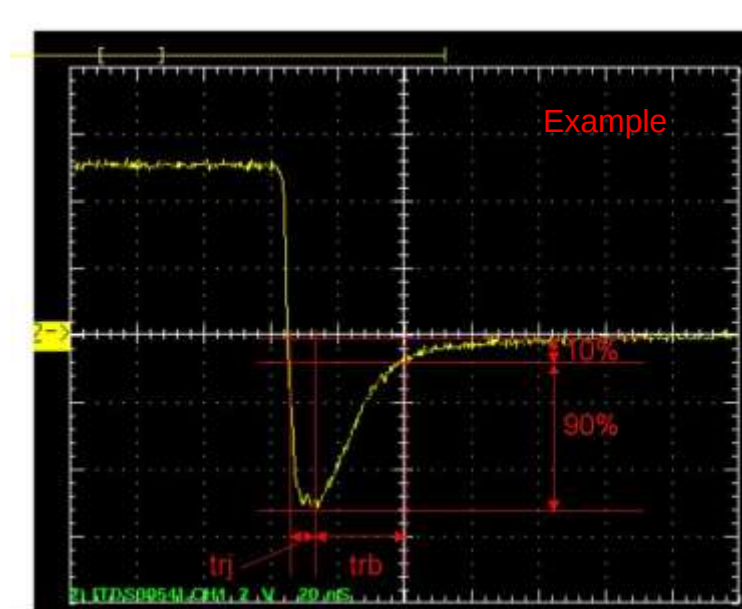
Reference



$t_{rj}=9.6(\text{ns})$

$t_{rb}=12.4(\mu\text{s})$

Conditions: $I_{fwd}=I_{rev}=0.2(\text{A})$, $R_I=50$



Relation between t_{rj} and t_{rb}